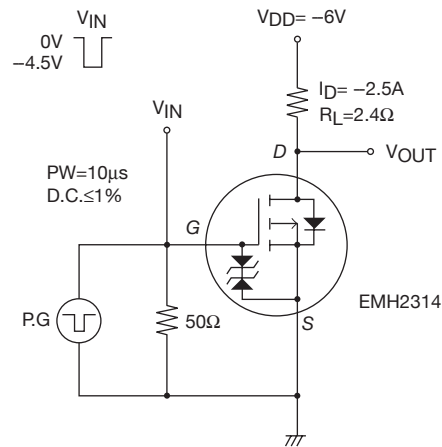


Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}$, $V_{GS} = 0\text{V}$	-12			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12\text{V}$, $V_{GS} = 0\text{V}$			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 8\text{V}$, $V_{DS} = 0\text{V}$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = -6\text{V}$, $I_D = -1\text{mA}$	-0.4		-1.3	V
Forward Transconductance	g_{FS}	$V_{DS} = -6\text{V}$, $I_D = -2.5\text{A}$		11		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -2.5\text{A}$, $V_{GS} = -4.5\text{V}$		28	37	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D = -1.5\text{A}$, $V_{GS} = -2.5\text{V}$		53	75	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D = -0.5\text{A}$, $V_{GS} = -1.8\text{V}$		133	200	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -6\text{V}$, $f = 1\text{MHz}$		1300		pF
Output Capacitance	C_{oss}			158		pF
Reverse Transfer Capacitance	C_{rss}			143		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		16		ns
Rise Time	t_r			77		ns
Turn-OFF Delay Time	$t_{d(off)}$			79		ns
Fall Time	t_f			58		ns
Total Gate Charge	Q_g	$V_{DS} = -6\text{V}$, $V_{GS} = -4.5\text{V}$, $I_D = -5\text{A}$		12		nC
Gate-to-Source Charge	Q_{gs}			3		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			2		nC
Forward Diode Voltage	V_{SD}	$I_S = -5\text{A}$, $V_{GS} = 0\text{V}$		-0.9	-1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
EMH2314-TL-H	EMH8	3,000pcs./reel	Pb-Free and Halogen Free

